



Serial No. 09/478,508

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS

Claim 16 has been amended as follows:

1 16. (Amended) A semiconductor device having a semiconductor chip,
2 first electrodes formed on said semiconductor chip,
3 barrier metals formed on said first electrodes and having laminated structures, and
4 a plurality of second protruded electrodes, which serve as external connection terminals,
5 formed on said barrier metals, wherein said barrier metals comprising:
6 a lowermost conductive metal layer laminated on said first electrodes, said lowermost
7 conductive metal layer having a joining property with said first electrodes;
8 an intermediate conductive metal layer laminated on said lowermost conductive metal
9 layer, said intermediate conductive metal layer ~~comprising one or more layers and having a joining~~
10 ~~property with said lowermost conductive metal layer, said intermediate conductive metal layer~~
11 ~~having at least one layer serving as a barrier layer for preventing said protruded electrodes from~~
12 ~~diffusing into said intermediate conductive metal layer~~ being made of nickel (Ni); and
13 an uppermost conductive metal layer laminated on said one or more intermediate
14 conductive metal layers, said uppermost conductive metal layer being made of a material which
15 easily alloys with the material of said intermediate conductive metal layers and which has resistance
16 to oxidation, ~~wherein~~ said uppermost conductive metal layer is being made of a metal selected from

17 the group consisting of gold (Au), platinum (Pt), palladium (Pd), silver (Ag) and rhodium (Rh) or
18 of an alloy containing a metal selected from the group consisting of gold (Au), platinum (Pt),
19 palladium (Pd), silver (Ag) and rhodium (Rh).